

DS3414-1.2

DC4200 Series

SILICON VHF/UHF TUNING VARACTORS

DC4200 Series varactors are abrupt junction devices of planar-epitaxial construction. They are intended for electronic tuning and other frequency control applications in the VHF/UHF region. Device performance has been optimised by careful attention to processing techniques. The use of oxide/nitride passivation produces varactors with good stability and low leakage.

Low substrate resistance and optimised metal contact schemes help to minimise series resistance, resulting in high values of Q. Capacitance values (C_T - 4V) from 2.2 to 350pF are available in a range of appropriate packages.

FEATURES

- # High Q
- Large tuning range
- Designed for high reliability
- Wide range of capacitance values
- High capacitance tolerance
- Many special selections available

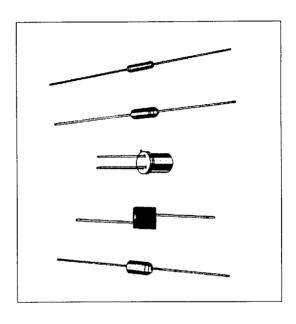
DC4200 Series varactors are designed for high quality and high reliability applications. GEC Plessey Semiconductors has a proven record of supplying high reliability devices for military programmes. Devices are produced to meet the strict standards of U.K. Ministry of Defence approval to NATO AQAP-1(Edit.3).

In addition, DB4200 series varactors are available to CECC 50 077. To qualify, devices undergo severe mechanical and environmental testing* similar to that required to MIL 202. This is backed up by long term reliability testing.

MTBF's (Mean Time Before Failure) of >10⁷ hours are typical. Special screening can be performed on most device types and can be tailored to meet specific requirements.

Contact our local representatives for further information.

*BS2011 and IEC 68 series test programme.



DC4200 Series

LIMITING CONDITIONS OF USE

| Maximum Reverse Voltage (V _R) | 60V | | |
|---|----------------|--|--|
| Storage Temperature Range | -55° to +150°C | | |
| Operating Temperature Range | -55° to +100°C | | |

ELECTRICAL CHARACTERISTICS

At T_{amb} = 25°C

The table of electrical characteristics gives an appreciation of the range of varactors available. However, the range can be extended to meet individual customer requirements. Special features available include:

- Tighter tolerance and matched sets
- 100% burn-in
- Choice of minimum breakdown voltage
- Special reliability testing
- Higher Q
- Wider bandwidth tuning

| Type No. | Outline No. | Total Capacitance C _T ±10% (pF) | Capacitance Ratio (min) | Breakdown Voltage V _B (V) (min) | Quality Factor Q (min) | Test Frequency f (MHz) | Reverse Voltage V _R (V) |
|-------------|----------------|--|------------------------------------|--|------------------------------|------------------------------|--|
| DC4255B | 35 | 2.2 | 2.5 | 60 | 550 | 50 | -4.0 |
| DC4256B | 35 | 3.3 | 2.7 | 60 | 450 | 50 | -4.0 |
| DC4257B | 07 | 4.7 | 2.8 | 60 | 450 | 50 | -4.0 |
| DC4210B | 07 | 6.8 | 2.9 | 60 | 450 | 50 | -4.0 |
| DC4211B | 07 | 8.2 | 2.9 | 60 | 400 | 50 | -4.0 |
| DC4212B | 07 | 10.0 | 3.0 | 60 | 350 | 50 | -4.0 |
| DC4213B | 07 | 12.0 | 3.0 | 60 | 350 | 50 | -4.0 |
| DC4214B | 07 | 15.0 | 3.1 | 60 | 300 | 50 | -4.0 |
| DC4215B | 07 | 18.0 | 3.1 | 60 | 250 | 50 | -4.0 |
| DC4216B | 07 | 22.0 | 3.2 | 60 | 250 | 50 | -4.0 |
| DC4217B | 07 | 27.0 | 3.2 | 60 | 200 | 50 | -4.0 |
| DC4218B | 07 | 33.0 | 3.2 | 60 | 200 | 50 | -4.0 |
| DC4224B | 07 | 39.0 | 3.2 | 60 | 200 | 50 | -4.0 |
| DC4225B | 07 | 47.0 | 3.2 | 60 | 200 | 50 | -4.0 |
| DC4226B | 14 | 56.0 | 3.2 | 60 | 120 | 50 | -4.0 |
| DC4227B | 14 | 68.0 | 3.2 | 60 | 120 | 50 | -4.0 |
| DC4228B | 14 | 80.0 | 3.2 | 60 | 100 | 50 | -4.0 |
| DC4229D | 14 | 80.0 | 3.2 | 100 | 200 | 50 | -4.5 |
| DC4229F | 14 | 57.0* | 3.85* | 120 | 240 | 50 | -15.0 |
| DC4232B | 18 | 100 | 3.2 | 60 | 200 | 10 | -4.0 |
| DC4233B | 18 | 120 | 3.2 | 60 | 200 | 10 | -4.0 |
| DC4234B | 18 | 150 | 3.2 | 60 | 200 | 10 | -8.0 |
| DC4298 | 10 | 200 | 3.2 | 100 | 200 | 25 | -8.0 |
| DC4299 | 10 | 335 | 3.2 | 100 | 200 | 25 | -8.0 |
| DC4244C | 78 | 350 | 3.2 | 90 | 750 | 1 1 | -4.0 |
| Test Co | onditions | V = 4V f = 1MHz *V = 8V | 4V to 60V f = 1MHz *4V = 85V | I _R = 10μΑ | | | **** |

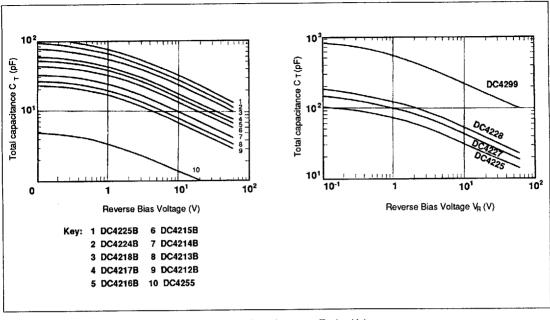


Figure 1. Typical Capacitance vs. Tuning Voltage

CAPACITANCE LAW

The total capacitance C_T at an applied voltage V for a varactor is given by:

$$C_T = A (V + \emptyset)^{-\gamma}$$

where:

A = a constant relating to epilayer doping level and diode area

Ø = built in junction potential (0.65V for silicon)

 $\gamma = 0.45 \text{ to } 0.475$

Q FACTOR

Q can be calculated from

$$Q = \frac{1}{2\pi fRC}$$

and is normally measured and specified at 50MHz for these diodes.

Q at any other frequency can be approximated by

$$Q(f_2) = \frac{f_1}{f_2} (Q(f_1))$$

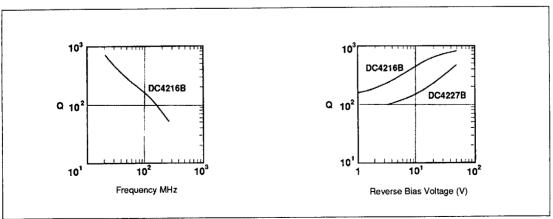


Figure 2. Typical Q vs. Frequency

Figure 3. Typical Q vs. Reverse Bias Voltage

